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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Setsuo NAKAJIMA et al. Art Unit : 2812
Serial No. : 09/768,618 Examiner : Stanetta Isaac
Filed : January 25, 2001
Title : SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

Commissioner for Patents
Washington, D.C. 20231

RESPONSE

In response to the action mailed August 22, 2002, please amend the application as follows:

In the claims:Please amend claims 13 and 20-24 as follows:

-- 13. (Amended) A method of manufacturing a semiconductor device comprising:

- a1*
- ✓ forming a heat absorbing layer in an island form over a substrate;
 - ✓ forming an insulating film over said heat absorbing layer;
 - ✓ forming a non-single crystalline semiconductor film on said insulating film;
 - ✓ irradiating said non-single crystalline semiconductor film with light so that said semiconductor film is melted and solidified; and
 - ✓ patterning said semiconductor film into a semiconductor island, the semiconductor island not overlapping with the heat absorbing layer,
 - ✓ wherein a channel length direction of the semiconductor island is parallel to a longitudinal outer edge of said heat absorbing layer.

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20. (Amended) A method of manufacturing a semiconductor device comprising:
✓ forming a heat absorbing layer comprising a metal over a substrate;
✓ forming a first insulating film over said heat absorbing layer;
✓ forming a non-single crystalline semiconductor film on said first insulating film;

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